



The ZMS035N08HB combines advanced trench MOSFET technology with a low resistance package to provide

T_C =25

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V _{DS}	80	V
Gate-Source Voltage	V _{GS}	±20	V
Continuous Drain Current	I _{D@TC=25}	140	A
	I _{D@TC=75}	106.4	A
	I _{D@TC=100}	88.2	A
Pulsed Drain Current	I _{DM}	320	A
Total Power Dissipation(TC=25)	P _{D@TC=25}	150	W
Operating Junction Temperature	T _J	-55 to 150	
Storage Temperature	T _{STG}	-55 to 150	
Single Pulse Avalanche Energy@L=0.1mH	E _{AS}	125	mJ
Avalanche Current@L=0.1mH	I _{AS}	50	A

**Thermal resistance**

Parameter	Symbol	Min.	Typ.	Max.	Unit
Thermal resistance, junction - case	R_{thJC}	-	-	0.75	° C/W
Thermal resistance, junction - ambient	R_{thJA}	-	-	70	° C/W
Soldering temperature, wavesoldering for 10s	T_{sold}	-	-	265	° C

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=250\mu A$	80			V
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS}=V_{DS}, I_D=250\mu A$	2		4	V
Drain-Source Leakage Current	I_{DSS}	$V_{DS}=80V, V_{GS}=0V$			1.0	μA
Gate- Source Leakage Current	I_{GSS}	$V_{GS}=\pm 20V, V_{DS}=0V$			100	nA
Static Drain-source On Resistance	$R_{DS(ON)}$	$V_{GS}=10V, I_D=30A$				
Forward Transconductance	g_{FS}	$V_{DS}=10V, I_D=40A$				
Source-drain voltage	V_{SD}	$I_S=30A$				

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Input capacitance	C_{iss}	$f = 1MHz$	-	3100	-	μF

Fig.1 Gate-Charge Characteristics

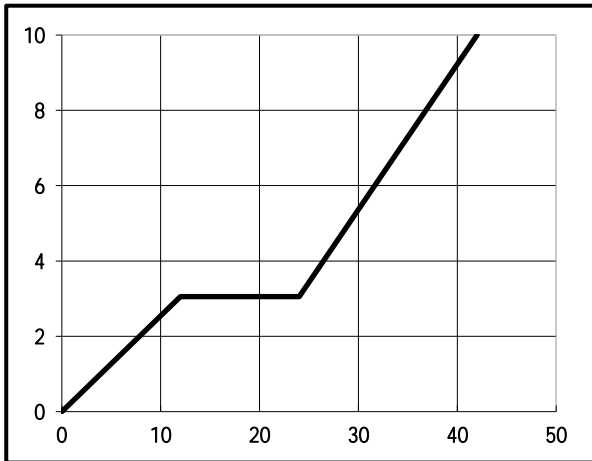


Fig.2 Capacitance Characteristics

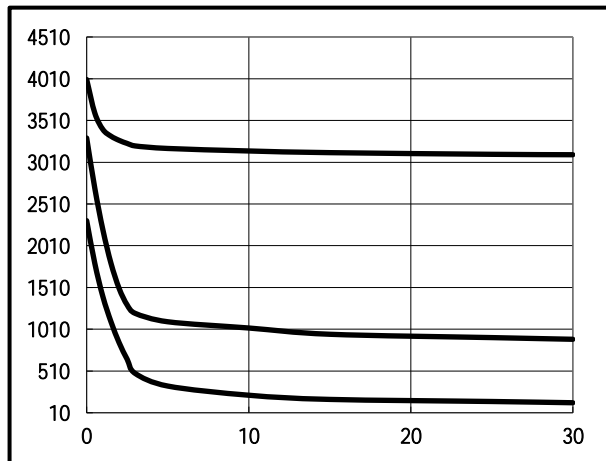


Fig.3 Power Dissipation

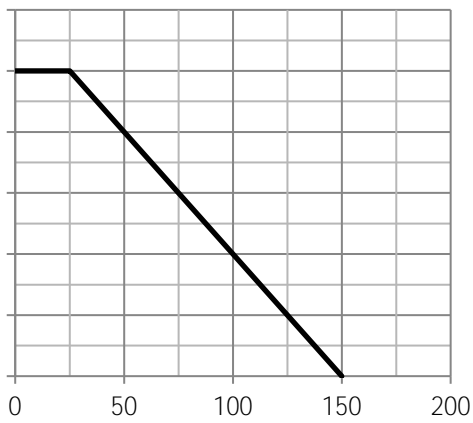


Fig.4 Typical output Characteristics

Fig.5 Threshold Voltage V.S Junction Temperature

Fig.6 Resistance V.S Drain Current



Fig.7 On-Resistance VS Gate Source Voltage

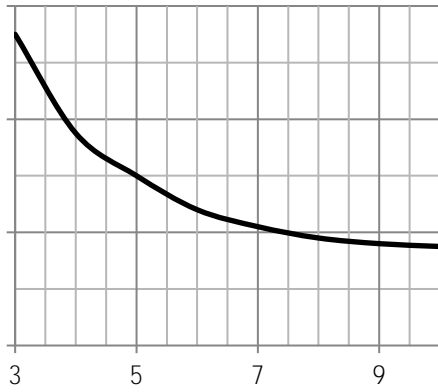


Fig.8 On-Resistance V.S Junction Temperature

Fig.9 Switching Time Measurement Circuit

Fig.10 Gate Charge Waveform

Fig.11 Switching Time Measurement Circuit

Fig.12 Gate Charge Waveform



Dimensions (TO-263)

Unit mm